

**Description**

The SX150N06NF uses advanced technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 10V. This device is suitable for use as a Battery protection or in other Switching application.

**General Features**

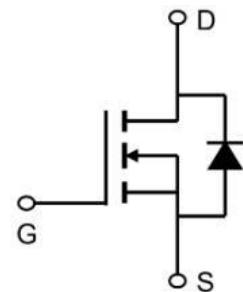
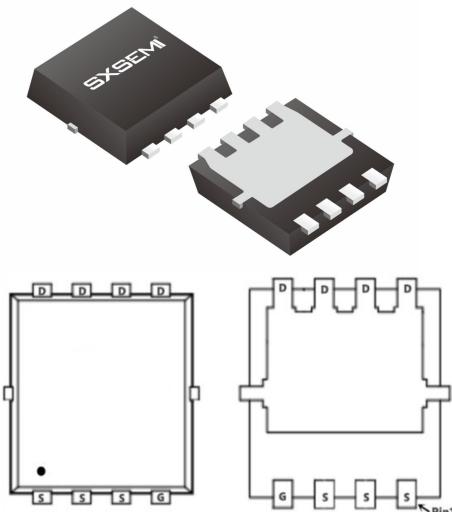
$V_{DS} = 60V$   $I_D = 150A$

$R_{DS(ON)} < 2.5m\Omega$  @  $V_{GS}=10V$

**Application**

Battery protection

UPS

**PDFN5\*6-8L****Absolute Maximum Ratings ( $T_c=25^\circ C$  unless otherwise noted)**

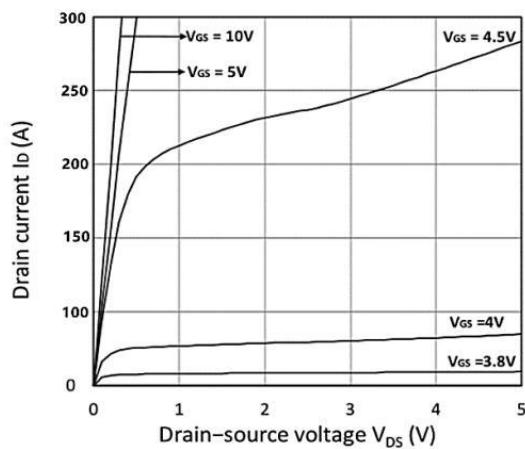
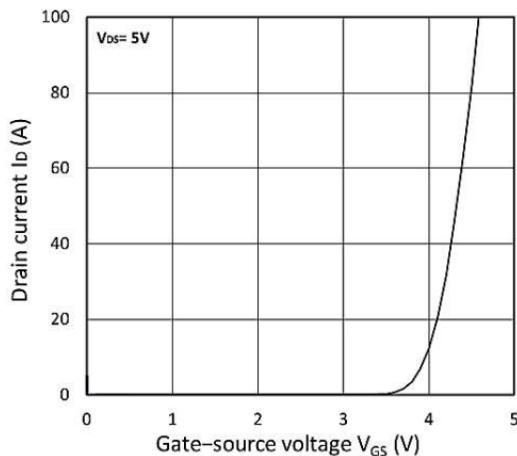
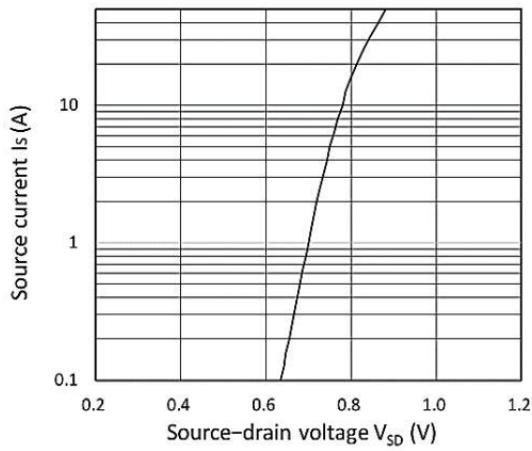
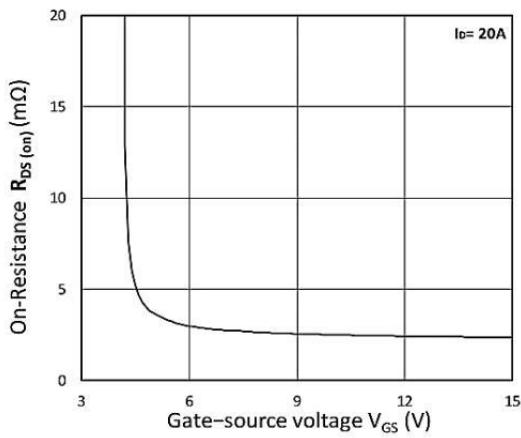
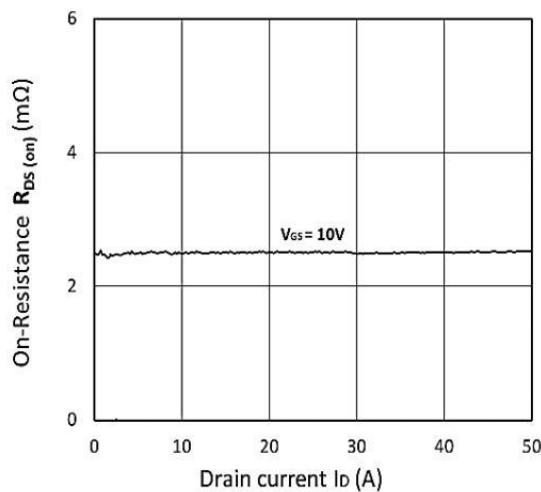
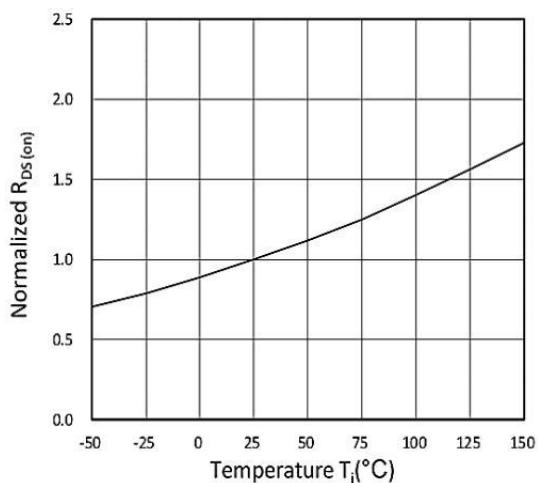
Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	60	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D @ T_c=25^\circ C$	Continuous Drain Current <sup>1,6</sup>	150	A
$I_D @ T_c=100^\circ C$	Continuous Drain Current <sup>1,6</sup>	105	A
$IDM$	Pulsed Drain Current <sup>2</sup>	450	A
$EAS$	Single Pulse Avalanche Energy <sup>3</sup>	585	mJ
$IAS$	Avalanche Current	55	A
$P_D @ T_c=25^\circ C$	Total Power Dissipation <sup>4</sup>	168	W
$T_{STG}$	Storage Temperature Range	-55 to 150	°C
$T_J$	Operating Junction Temperature Range	-55 to 150	°C
$R_{eJA}$	Thermal Resistance Junction-Ambient <sup>1</sup>	25	°C/W
$R_{eJC}$	Thermal Resistance Junction-Case <sup>1</sup>	1.5	°C/W

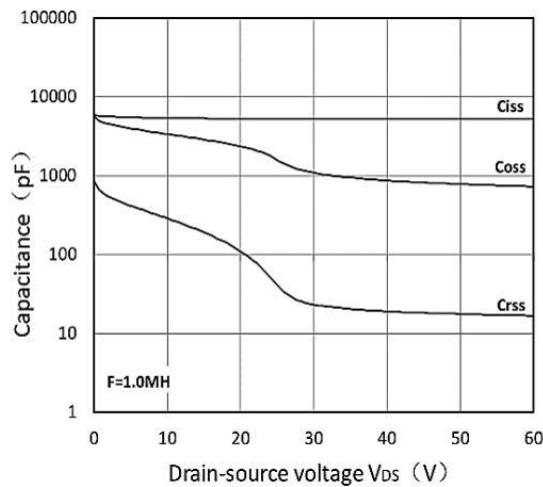
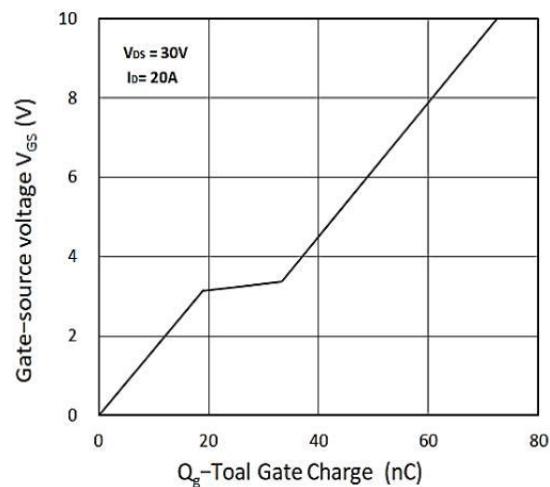
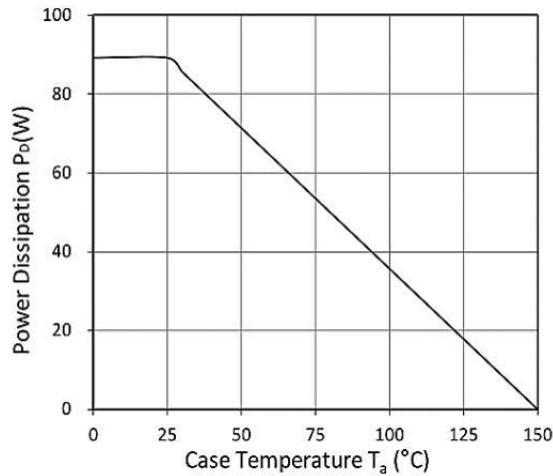
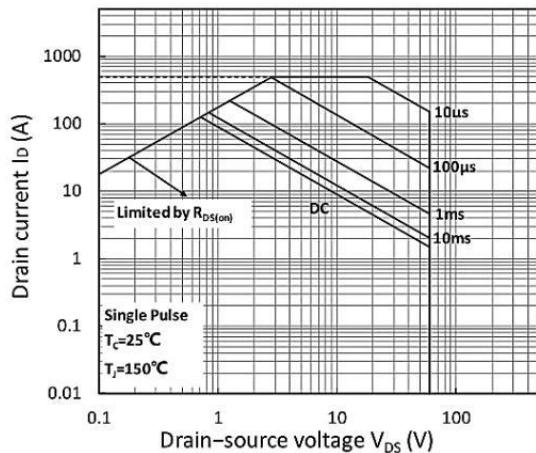
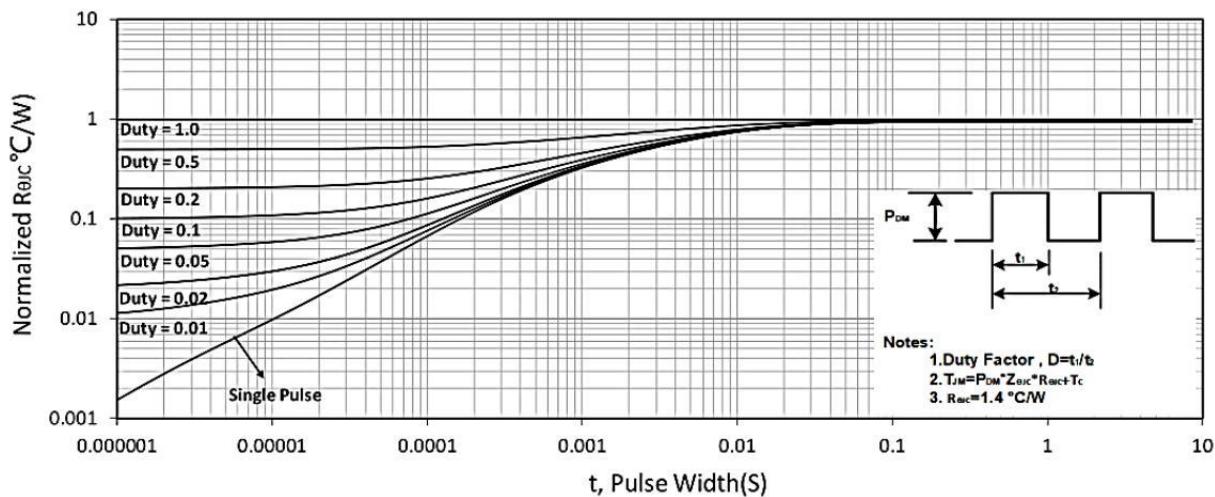
**Electrical Characteristics (T<sub>J</sub>=25°C, unless otherwise noted)**

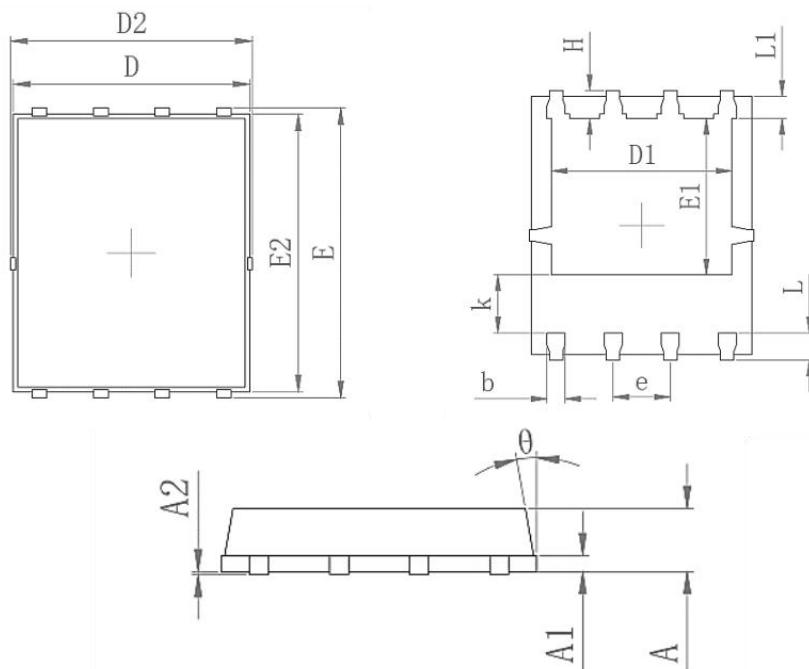
Symbol	Parameter	Test Conditions	Min	Type	Max	Unit
V(BR)DSS	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	60	68	-	V
IGSS	Gate-body Leakage Current	V <sub>DS</sub> = 0V, V <sub>GS</sub> = ±20V	-	-	±100	nA
IDSS T <sub>J</sub> =25°C	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 60V, V <sub>GS</sub> = 0V	-	-	1	μA
IDSS T <sub>J</sub> =100°C	Zero Gate Voltage Drain Current		-	-	100	
V <sub>GS</sub> (th)	Gate-Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	1.0	1.75	2.5	V
RDS(on)	Drain-Source On-Resistance <sup>4</sup>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 20A	-	1.98	2.7	mΩ
RDS(on)	Drain-Source On-Resistance <sup>4</sup>	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 10A	-	2.7	3.5	mΩ
g <sub>f</sub> s	Forward Transconductance <sup>4</sup>	V <sub>DS</sub> = 5V, I <sub>D</sub> = 20A	-	78	-	S
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V, f = 1MHz	-	5245	-	pF
C <sub>oss</sub>	Output Capacitance		-	1090	-	
C <sub>rss</sub>	Reverse Transfer Capacitance		-	25	-	
R <sub>G</sub>	Gate Resistance	f = 1MHz	-	2.2	-	Ω
Q <sub>g</sub>	Total Gate Charge	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 30V, I <sub>D</sub> = 20A	-	72.5	-	nC
Q <sub>gs</sub>	Gate-Source Charge		-	19.5	-	
Q <sub>gd</sub>	Gate-Drain Charge		-	14	-	
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>GS</sub> = 10V, V <sub>DD</sub> = 30V, R <sub>G</sub> = 3Ω, I <sub>D</sub> = 20A	-	26.5	-	ns
t <sub>r</sub>	Rise Time		-	15	-	
t <sub>d(off)</sub>	Turn-off Delay Time		-	73	-	
t <sub>f</sub>	Fall Time		-	18	-	
t <sub>rr</sub>	Body Diode Reverse Recovery Time	I <sub>F</sub> = 20A, dI/dt = 100A/μs	-	25	-	ns
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge		-	90	-	nC
V <sub>SD</sub>	Diode Forward Voltage <sup>4</sup>	I <sub>S</sub> = 20A, V <sub>GS</sub> = 0V	-	-	1.2	V
I <sub>S</sub>	Continuous Source Current T <sub>c</sub> =25°C		-	-	125	A

**Note :**

- 1、The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.
- 2、The data tested by pulsed , pulse width .The EAS data shows Max. rating .
- 3、The power dissipation is limited by 175°C junction temperature
- 4、EAS condition: TJ=25°C, VDD=48V, VG=10V, RG=25Ω, L=0.1mH, IAS= 55A
- 5、The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

**Typical Characteristics****Figure 1. Output Characteristics****Figure 2. Transfer Characteristics****Figure 3. Forward Characteristics of Reverse****Figure 4. RDS(ON) vs. VGS****Figure 5. R DS(ON) vs. ID****Figure 6. Normalized R DS(on) vs. Temperature**

**Typical Characteristics****Figure 7. Capacitance Characteristics****Figure 8. Gate Charge Characteristics****Figure 9. Power Dissipation****Figure 10. Safe Operating Area****Figure 11. Normalized Maximum Transient Thermal Impedance**

**Package Mechanical Data-PDFN5X6-8L-XZT Single**

Symbol	Common	
	mm	
	Mim	Max
A	0.90	1.10
A1	0.254 REF	
A2	0-0.05	
D	4.824	4.976
D1	3.910	4.110
D2	4.944	5.076
E	5.924	6.076
E1	3.375	3.575
E2	5.674	5.826
b	0.350	0.450
e	1.270	
L	0.534	0.686
L1	0.424	0.576
K	1.190	1.390
H	0.549	0.701
Φ	8 °	12 °

**Package Marking and Ordering Information**

Product ID	Pack	Marking	Qty(PCS)
TAPING	PDFN5*6-8L		5000